

AMENDMENTS TO THE SPECIFICATION:

Page 6, amend paragraph [0014] as:

[0014] FIG. 1 shows a cross-sectional view of the bonding structure with a buffer layer before bonding according to the invention. In this embodiment, there are metal pads 103a and 103b on a surface of the first substrate 101 shown in the upper figure of FIG. 1. A protection layer 105 is covered on that surface of the first substrate 101. A first adhesive metal layer 110 is formed on the metal pads 103a and 103b. Buffer layers 107, 107a and 107b are respectively coated on the protection layer 105 and the first adhesive metal layer 110 over the metal pads 103a and 103b. A first metal layer 109 covers buffer layers 107, 107a and 107b.

Pages 6-7, amend paragraph [0015] as:

[0015] Metal pads 103a and 103b are used as conducting circuit for the first substrate 101. They can be made of aluminum (Al) or copper (Cu). The protection layer 105 protects the integrated circuit on the first substrate 101. The first substrate can be a ~~silicone~~ silicon (Si) substrate. The material for the buffer layer can be polyimide. The material for the first metal layer can be chosen from one of gold (Au), aluminum or copper. It is worthy to mention that the buffer layer coated on the first adhesive metal layer over the metal pads and the buffer layer on the protection layer are independently distributed in the embodiment.

Page 7, amend paragraph [0020] as:

[0020] FIG. 4 illustrates another cross-sectional view of the bonding structure with a buffer layer before bonding according to the invention. The difference between this embodiment and the embodiment illustrated in FIG. 1 is that the buffer layer coated on the first adhesive metal layer over the metal pads and the buffer layer on the protection layer are connected, as shown in label 401 of FIG. 4.